

			20	69.8	22%
	9.6	140%			
		6.8	24.6%		
4.6	27.4%	20	5.7		8%
		21Q1			20.4
	48%		4.0	252%	21Q1
	31.5%				
IGBT	SiC				
	20	44.8%	0.6		
		MOSFET		20	
20		IGBT		1	
	75%				
			1200V	650V SiC	
		6	SiC		
	8				
0.18 μ m BCD G3				0.11 μ m	
600V SOI		8		6	
					5G
8					
	21-23		1.07	1.36	1.70
1F	H	ш			21-22

21-23

1.07 1.36 1.70

21-

	2019A	2020A	2021E	2022E	2023E
:	1,931	6,866	11,076	11,695	12,704
	1,491	1,795	2,138	2,589	3,138
	52	52	61	74	90
	1,055	1,269	1,432	1,730	2,083
	564	932	935	938	942

	2019A	2020A	2021E	2022E	2023E
:	5,743	6,977	8,308	10,061	12,194
	4,431	5,061	5,711	6,898	8,305
	66	69	82	99	120
	112	106	125	146	171
	859	936	1,038	1,192	1,427

